

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions of claims in this application.

Please cancel claims 6-9 without prejudice or disclaimer, and add new claims 16-21, as follows:

- 1-9. (Canceled).
10. (New) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
 - placing the workpiece in a hermetically sealed process chamber;
 - introducing processing gas into the process chamber;
 - pressurizing the process chamber to a pressure equal to or higher than 500 mTorr;
 - etching the organic film; and
 - stopping the etching before the etching goes through the organic film.
11. (Previously Presented) A method of etching according to claim 10, wherein the processing gas comprises a gas comprising nitrogen atoms and a gas comprising hydrogen atoms.
12. (Previously Presented) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
 - placing the workpiece in a hermetically sealed process chamber;
 - introducing processing gas comprising a gas comprising nitrogen atoms and a gas comprising hydrogen atoms into the process chamber;
 - pressurizing the process chamber to a pressure between 500 - 800 mTorr;
 - etching the organic film; and

stopping the etching before the etching goes through the organic film.

13. (Previously Presented) A method of etching according to claim 12, wherein the gas comprising nitrogen atoms constitute N_2 and the gas comprising hydrogen atoms constitute H_2 .
14. (Previously Presented) A method of etching according to claim 12, wherein the processing gas further comprises Ar.
15. (Previously Presented) A method of etching according to claim 13, wherein the processing gas further comprises Ar.
16. (New) A method of etching according to claim 10, wherein the method is a damascene process.
17. (New) A method of etching according to claim 10, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
18. (New) A method of etching according to claim 10, wherein etching the organic film etches the organic film approximately halfway through the organic film.
19. (New) A method of etching according to claim 12, wherein the method is a damascene process.
20. (New) A method of etching according to claim 12, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
21. (New) A method of etching according to claim 12, wherein etching the organic film etches the organic film approximately halfway through the organic film.

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AMENDMENTS TO THE DRAWINGS:

Applicants submit herewith a Replacement Sheet for Fig. 4, containing the drawing correction rendered by a Request for Approval of Drawing Change filed on June 10, 2003 and approved by the Examiner in the Office Action of July 1, 2003.

Thus, Applicants respectfully request that the previously submitted drawing for Fig. 4 be replaced with the Replacement Sheet concurrently filed herewith.

Attachments: Replacement Sheet of drawing containing Fig. 4.

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